



BSS138

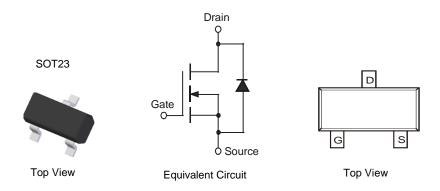
N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 @3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)



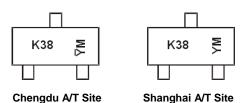
Ordering Information (Note 5)

Part Number	Qualification	Case	Packaging
BSS138-7-F	Commercial	SOT23	3000/Tape & Reel
BSS138-13-F	Commercial	SOT23	10000/Tape & Reel
BSS138Q-7-F	Automotive	SOT23	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



K38 = Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test Site) \overline{Y} M = Date Code Marking for CAT (Chengdu Assembly/ Test Site) Y or \overline{Y} = Year (ex: E = 2017)

M = Month (ex: 9 = September)

Date Code Kev

Date Code Ney															
Year	1998	1999	2000		2002	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	J	K	L		N	D	Е	F	G	Н	I	J	K	L	М
Month	Jan	Fe	b	Mar	Apr	May	Ju	n	Jul	Aug	Sep	Oc	t	Nov	Dec
Code	1	2		3	4	5	6	;	7	8	9	0		N	D



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

C	Characteristic	Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	50	V
Drain-Gate Voltage R _{GS} ≤ 2	20ΚΩ	V_{DGR}	50	V
Gate-Source Voltage Continuous		\/	±20	V
Gate-Source Voltage	Non Repetitive, Pulse Width<50μs	V_{GSS}	±40	V
Drain Current	Continuous	I _D	200	mA
Pulsed Drain Current (10µs	s Pulse Duty Cycle = 1%)	I _{DM}	1	A

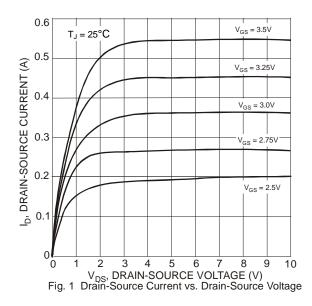
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

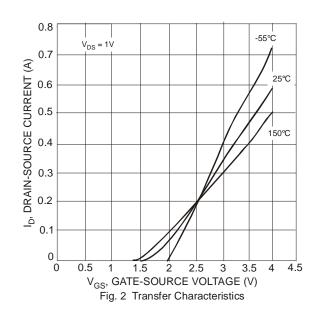
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P_{D}	300	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	417	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)		•		•	•		
Drain-Source Breakdown Voltage	BV _{DSS}	50	75	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_		0.5	μΑ	$V_{DS} = 50V, V_{GS} = 0V$	
Gate-Body Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.5	1.2	1.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		1.4	3.5	Ω	$V_{GS} = 10V, I_D = 0.22A$	
Forward Transconductance	g _{FS}	100	_	_	mS	$V_{DS} = 25V$, $I_D = 0.2A$, $f = 1.0KHz$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	Ciss	_		50	pF		
Output Capacitance	Coss	_		25	pF	$V_{DS} = 10V, V_{GS} = 0V, f = 1.0MHz$	
Reverse Transfer Capacitance	C_{rss}	_	_	8.0	pF	1	
SWITCHING CHARACTERISTICS							
Turn-On Delay Time	t _{D(ON)}			20	ns	V 20V I 0.24 B 500	
Turn-Off Delay Time	t _{D(OFF)}	_		20	ns	$V_{DD} = 30V, I_D = 0.2A, R_{GEN} = 50\Omega$	

Notes:





^{6.} Device mounted on FR-4 PCB 1.0 x 0.75 x 0.062 inch pad layout as shown on Diodes Incorporated's suggested pad layout, which can be found on our website at http://www.diodes.com/package-outlines.html.7. Short duration pulse test used to minimize self-heating effect.



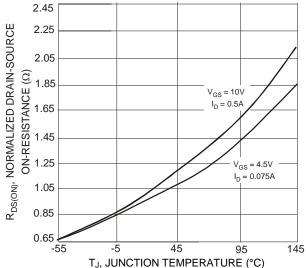


Fig. 3 Drain-Source On-Resistance vs. Junction Temperature

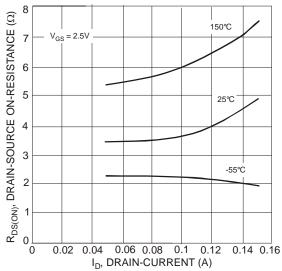


Fig. 5 Drain-Source On-Resistance vs. Drain-Current

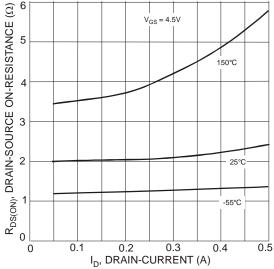
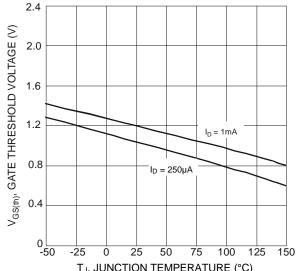


Fig. 7 Drain-Source On-Resistance vs. Drain-Current



T_J, JUNCTION TEMPERATURE (°C) Fig. 4 Gate Threshold Variation vs. Junction Temperature

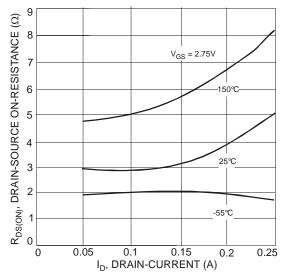


Fig. 6 Drain-Source On-Resistance vs. Drain-Current

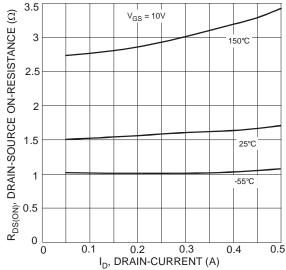
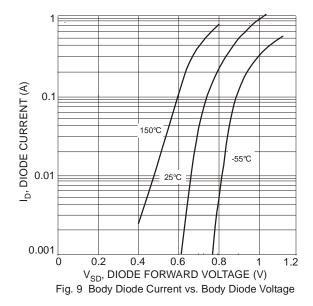
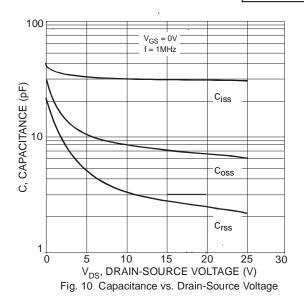


Fig. 8 Drain-Source On Resistance vs. Drain-Current

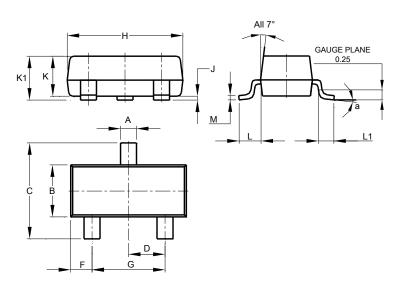






Package Outline Dimensions

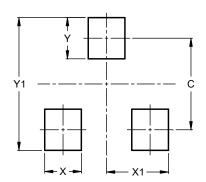
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
M	0.085	0.150	0.110					
а	0°	8°						
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2017, Diodes Incorporated

www.diodes.com

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Diodes Incorporated manufacturer:

Other Similar products are found below:

614233C 648584F MCH3443-TL-E MCH6422-TL-E FDPF9N50NZ FW216A-TL-2W FW231A-TL-E APT5010JVR NTNS3A92PZT5G IRF100S201 JANTX2N5237 2SK2464-TL-E 2SK3818-DL-E FCA20N60_F109 FDZ595PZ STD6600NT4G FSS804-TL-E 2SJ277-DL-E 2SK1691-DL-E 2SK2545(Q,T) 405094E 423220D MCH6646-TL-E TPCC8103,L1Q(CM 367-8430-0972-503 VN1206L 424134F 026935X 051075F SBVS138LT1G 614234A 715780A NTNS3166NZT5G 751625C 873612G IRF7380TRHR IPS70R2K0CEAKMA1 RJK60S3DPP-E0#T2 RJK60S5DPK-M0#T0 APT5010JVFR APT12031JFLL APT12040JVR DMN3404LQ-7 NTE6400 JANTX2N6796U JANTX2N6784U JANTXV2N5416U4 SQM110N05-06L-GE3 SIHF35N60E-GE3 2SK2614(TE16L1,Q)